

SGM3003 Ultra Low ON-Resistance, Low Voltage, SPDT Analog Switch

GENERAL DESCRIPTION

The SGM3003 is a single, low on-resistance, low voltage, bidirectional, single-pole/double-throw (SPDT) CMOS analog switch designed to operate from a single +1.8V to +5.5V supply. Targeted applications include battery powered equipment that benefit from low R_{ON} (0.5 Ω) and fast switching speeds (t_{ON} = 21ns, t_{OFF} = 9ns).

The on resistance profile is very flat over the full analog signal range. This ensures excellent linearity and low distortion when switching audio signals.

SGM3003 has one normally open switch and one normally closed switch, Each switch conducts equally well in both directions when on.

SGM3003 is available in a Green MSOP-8 package.

APPLICATIONS

Medical Equipment

Battery powered, Handheld, and Portable Equipment
Cellular/mobile Phones
Laptops, Notebooks, Palmtops
Communication Systems
Sample-and-Hold Circuits
Audio Signal Routing
Audio and Video Switching
Portable Test and Measurement

FEATURES

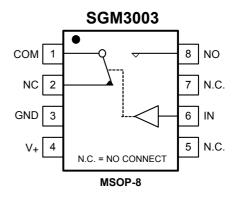
- Low Voltage Operation: 1.8V to 5.5V
- Low On-Resistance: 0.5Ω (TYP)
- Low On-Resistance Flatness
- -3dB Bandwidth: 30MHz
- Fast Switching Times (V₊ = 5V)

ton 21ns

tope 9ns

- Rail-to-Rail Operation
- Typical Power Consumption (<0.01µW)
- TTL/CMOS Compatible
- Microsize Package

PIN CONFIGURATION (TOP VIEW)



FUNCTION TABLE

LOGIC	NC	NO
0	ON	OFF
1	OFF	ON

PACKAGE/ORDERING INFORMATION

MODEL	PIN- PACKAGE	TEMPERATURE SILL TIMES		PACKAGE MARKING	PACKAGE OPTION	
SGM3003	MSOP-8	-40℃ to +125℃	SGM3003XMS/TR	SGM3003XMS	Tape and Reel, 3000	

ABSOLUTE MAXIMUM RATINGS

V+ to GND	0.3V to 6V
Analog, Digital voltage range (1)	0.3V to (V ₊) + 0.3V
Continuous Current NO, NC, or COM	±300mA
Peak Current NO, NC, or COM	±500mA
Operating Temperature Range	40°C to +125°C
Junction Temperature	150°C
Storage Temperature	65°C to +150°C

Package Thermal Resistance @ T _A = 25°C	
MSOP-8, θ _{JA}	216°C/W
Lead Temperature (soldering, 10s)	260°C
ESD Susceptibility	
HBM	2000V
MM	400V

NOTES:

- 1. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- 2. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

SGMICRO reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time. Please contact SGMICRO sales office to get the last datasheet.

PIN DESCRIPTION

NAME	PIN	FUNCTION
V ₊	4	Power supply
GND	3	Ground
IN	6	Digital control pin to connect the COM terminal to the NO or NC terminals
COM	1	Common terminal
NO	8	Normally-open terminal
NC	2	Normally-closed terminal
N.C.	5, 7	No internal connection

NOTE: NO, NC and COM terminals may be an input or output.



SGM3003

ELECTRICAL CHARACTERISTICS

 $(V_+ = +5V \pm 10\%, GND = 0V, T_A = -40^{\circ}C$ to $+125^{\circ}C$. Typical values are at $T_A = +25^{\circ}C$, unless otherwise noted.)

		CONDITIONS		SGM3003			
PARAMETER	SYMBOL			+25℃	-40℃ to +125℃	UNITS	MIN/ MAX
ANALOG SWITCH	1			1			
Analog Signal Range	V _{NO} , V _{NC} , V _{COM}				0	V	MIN
7 thaiog Oighai Range	VNO, VNC, VCOM				V ₊	V	MAX
On-Resistance	Ron	$0 \le V_{NO} \text{ or } V_{NC} \le V_+, I_C$	_{OM} = -10mA,	0.5		Ω	TYP
	. ton	Test Circuit 1		0.9	1.1	Ω	MAX
On-Resistance Flatness	R _{FLAT(ON)}	$0 \le V_{NO}$ or $V_{NC} \le V_+$, I_C Test Circuit 1	_{OM} = -10mA,	0.13	0.4	Ω	TYP MAX
LEAKAGE CURRENTS				1			1
Source OFF Leakage		V_{NO} or $V_{NC} = 4.5V/1V$,	V _{COM} = 1V/4.5V,	±4		nA	TYP
Current	I _{NC(OFF)} , I _{NO(OFF)}	V_+ = +5.5V ,Test Circu		±10	±1000	nA	MAX
Channel ON Leakage	I _{NC(ON)} , I _{NO(ON)} ,	V_{NO} or $V_{NC} = V_{COM} = 1$		±4		nA	TYP
Current	I _{COM(ON)}	V ₊ = +5.5V , Test Circu	uit 3	±10	±1000	nA	MAX
DIGITAL INPUTS		,					
Input High Voltage	V _{INH}				2.4	V	MIN
Input Low Voltage	V _{INL}				0.8	V	MAX
Input Current	I _{INL} or I _{INH}	V _{IN} = V _{INH} or V _{INL}		±0.01		μA	TYP
•				±0.1	±1	μA	MAX
DYNAMIC CHARACTERIS	TICS	T		1			ı
Turn-On Time	ton	V_{NO} or V_{NC} = 3V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4		21		ns	TYP
Turn-Off Time	toff	V_{NO} or V_{NC} = 3V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4		9		ns	TYP
Charge Injection	Q	C_L = 1.0nF, V_G = 0V, R_G = 0 Ω , Test Circuit 5		5		рC	TYP
Break-Before-Make Time Delay	t _D	V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 3V$, $R_L = 300\Omega$, $C_L = 35pF$, Test Circuit 6		10		ns	TYP
Off lookstion	0	$R_L = 50\Omega$, $C_L = 5pF$,	f = 100kHz	-55		dB	TYP
Off Isolation	O _{ISO}	Test Circuit 7	f = 10kHz	-75		dB	TYP
Total Harmonic Distortion	THD	f = 20Hz to 20kHz, V_{COM} = 3.5 V_{P-P} , R_L = 600Ω, C_L = 50pF		0.065		%	TYP
-3dB Bandwidth	BW	$R_L = 50\Omega$, $C_L = 5pF$, Test Circuit 8		30		MHz	TYP
Source OFF Capacitance	C _{NC(OFF)} , C _{NO(OFF)}			82		pF	TYP
Channel ON Capacitance	$C_{NC(ON)}, C_{NO(ON)}, C_{COM(ON)}$			380		pF	TYP
POWER REQUIREMENTS							
Power Supply Current	I+	V ₊ = +5.5V, V _{IN} = 0V o	r 5V	0.001		μΑ	TYP
. onor ouppry ourront	VT . 3.3 V, VIII - 3 V 31 3 V			1	μA	MAX	

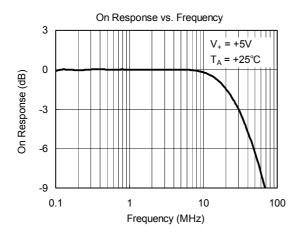
SGM3003

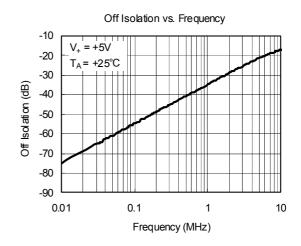
ELECTRICAL CHARACTERISTICS

 $(V_+ = +3V \pm 10\%, GND = 0V, T_A = -40^{\circ}C$ to $+125^{\circ}C$. Typical values are at $T_A = +25^{\circ}C$, unless otherwise noted.)

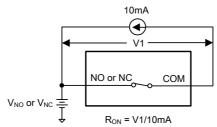
		CONDITIONS		SGM3003			
PARAMETER	SYMBOL			+25℃	-40℃ to +125℃	UNITS	MIN/ MAX
ANALOG SWITCH	1						1
Analog Signal Range	Var Var Var				0	V	MIN
Analog Signal Range	V_{NO}, V_{NC}, V_{COM}				V_{+}	V	MAX
On-Resistance	D	$0 \le V_{NO}$ or $V_{NC} \le V_+$, $I_{COM} = -10$ mA, Test Circuit 1		0.6		Ω	TYP
On-inesistance	R _{ON}			1.0	1.3	Ω	MAX
On-Resistance Flatness	R _{FLAT(ON)}	0 ≤ V _{NO} or V _{NC} ≤ V ₊ , I _{COM} = Test Circuit 1	-10mA,	0.18	0.4	Ω	TYP
LEAKAGE CURRENTS		Tool on out 1		0.3	0.4	Ω	MAX
		N N 0 (4) () (4) //0) /	±5		nA	TYP
Source OFF Leakage Current	I _{NC(OFF)} , I _{NO(OFF)}	V_{NO} or V_{NC} = 3V/1V, V_{COM} = V_{+} = +3.3V, Test Circuit 2	= 1V/3V,	±11	±1000	nA	MAX
Channel ON Leakage	I _{NC(ON)} , I _{NO(ON)} ,	V _{NO} or V _{NC} = V _{COM} = 1V or	3V	±5		nA	TYP
Current	I _{COM(ON)}	V_{+} = +3.3V , Test Circuit 3	OV,	±11	±1000	nA	MAX
DIGITAL INPUTS							
Input High Voltage	V _{INH}				2.0	V	MIN
Input Low Voltage	V _{INL}				0.4	V	MAX
Input Current	I _{INL} or I _{INH}	$V_{IN} = V_{INH}$ or V_{INL}		±0.01		μA	TYP
DYNAMIC CHARACTERIS					±1	μA	MAX
DINAMIC CHARACTERIS	1105	\\ -2\\ -2\\ D -2000	0.0 - 05-5				
Turn-On Time	t _{ON}	V_{NO} or V_{NC} = 2V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4		32		ns	TYP
Turn-Off Time	toff	V_{NO} or V_{NC} = 2V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4		20		ns	TYP
Charge Injection	Q	C_L = 1.0nF, V_G = 0V, R_G = 0 Ω , Test Circuit 5		10		pC	TYP
Break-Before-Make Time Delay	t _D	V_{NO1} or V_{NC1} = V_{NO2} or V_{NC2} = 2V, R _L = 300 Ω , C _L = 35pF, Test Circuit 6		12		ns	TYP
Off Isolation	0	$R_L = 50\Omega$, $C_L = 5pF$,	f = 100kHz	-55		dB	TYP
On Idolation	O _{ISO}	Test Circuit 7	f = 10kHz	-75		dB	TYP
Total Harmonic Distortion	THD	f = 20Hz to 20kHz, V_{COM} = 2 V_{P-P} , R_L = 600 Ω , C_L = 50pF		0.06		%	TYP
-3dB Bandwidth	BW	$R_L = 50\Omega$, $C_L = 5pF$, Test Circuit 8		30		MHz	TYP
Source OFF Capacitance	C _{NC(OFF)} , C _{NO(OFF)}			82		pF	TYP
Channel ON Capacitance	$C_{NC(ON)}, C_{NO(ON)}, C_{COM(ON)}$			380		pF	TYP
POWER REQUIREMENTS	22(0)	•					•
Devices Councils Councils		0.001		μA	TYP		
Power Supply Current	I+	$V_{+} = +3.3V$, $V_{IN} = 0V$ or $3V$			1	μA	MAX

TYPICAL PERFORMANCE CHARACTERISTICS

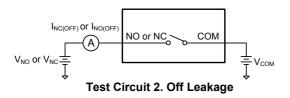


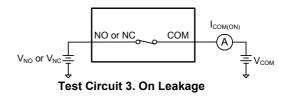


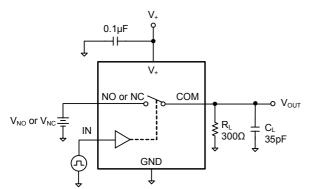
TEST CIRCUITS

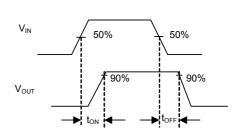


Test Circuit 1. On Resistance

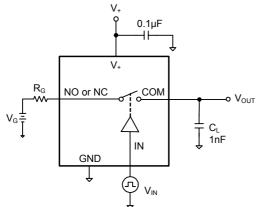


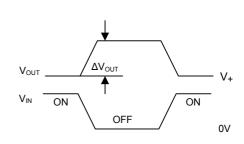






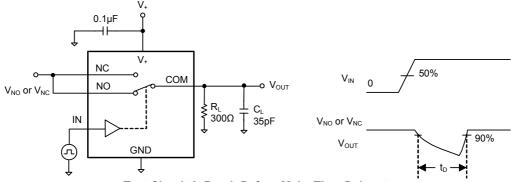
Test Circuit 4. Switching Times



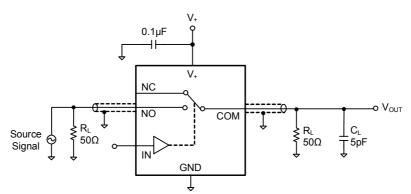


Test Circuit 5. Charge Injection

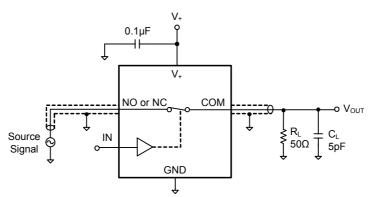
TEST CIRCUITS (Cont.)



Test Circuit 6. Break-Before-Make Time Delay, t_D



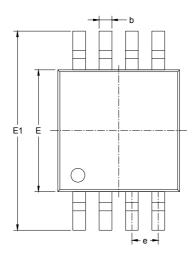
Test Circuit 7. Off Isolation

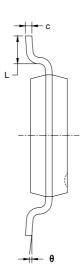


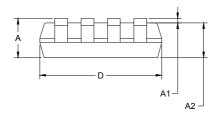
Test Circuit 8. -3dB Bandwidth

PACKAGE OUTLINE DIMENSIONS

MSOP-8







Symbol	Dimer In Milli		Dimensions In Inches		
	MIN	MAX	MIN	MAX	
Α	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
С	0.090	0.230	0.004	0.009	
D	2.900	3.100	0.114	0.122	
E	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
е	0.650 BSC		0.026	BSC	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	